

S1C33 Manual errata

ITEM: The A0RAM operating condition at the time of cash use			
Object manuals	Document codes	Items	Pages
S1C33L27 Technical Manual	411911901	12.2 Cache Configuration	12-2
<p>(Error)</p> <p>The method of using A0RAM as general-purpose RAM at the time of cash use is not clear.</p>			
<p>(Correct)</p> <p>Add the following contents.</p> <p>When you use A0RAM as general-purpose RAM at the time of cash use, please use it by the following allocation.</p>			
<div style="display: flex; justify-content: space-around; margin-top: 10px;"> <div style="text-align: center;"> <p>① Use instruction cache</p> </div> <div style="text-align: center;"> <p>② Use data cache</p> </div> <div style="text-align: center;"> <p>③ Use instruction and data cache</p> </div> </div>			

S1C33 Technical Manual Errata

ITEM: USI/USIL AC Characteristics					
Object manual	Document code	Object ITEM	Page		
S1C33L27 Technical Manual	411911901	32.8.4 USI/USIL AC Characteristics	32-11		
32-11					
(Error)					
SPI master mode (normal mode)					
Unless otherwise specified: LVDD = 1.65 to 1.95V, HVDD = 2.7 to 3.6V, VSS = 0V, Ta = -40 to 85°C					
Item	Symbol	Min.	Typ.	Max.	Unit
spi_ck cycle time	tSPCK	42 + tPCLK	-	-	ns
spi_di setup time	tSDS	42 + tPCLK	-	-	ns
SPI master mode (fast mode)					
Unless otherwise specified: LVDD = 1.65 to 1.95V, HVDD = 2.7 to 3.6V, VSS = 0V, Ta = -40 to 85°C					
Item	記号	Min.	Typ.	Max.	Unit
spi_ck cycle time	tSPCK	44	-	-	ns
spi_di setup time	tSDS	44	-	-	ns
(Correct)					
SPI master mode (normal mode)					
Unless otherwise specified: LVDD = 1.65 to 1.95V, HVDD = 2.7 to 3.6V, VSS = 0V, Ta = -40 to 85°C					
Item	Symbol	Min.	Typ.	Max.	Unit
spi_ck cycle time	tSPCK	(42 + tPCLK) x 2	-	-	ns
spi_di setup time	tSDS	42 + tPCLK	-	-	ns
SPI master mode (fast mode)					
Unless otherwise specified: LVDD = 1.65 to 1.95V, HVDD = 2.7 to 3.6V, VSS = 0V, Ta = -40 to 85°C					
Item	記号	Min.	Typ.	Max.	Unit
spi_ck cycle time	tSPCK	44 x 2	-	-	ns
spi_di setup time	tSDS	44	-	-	ns

S1C33 Series Technical Manual Errata

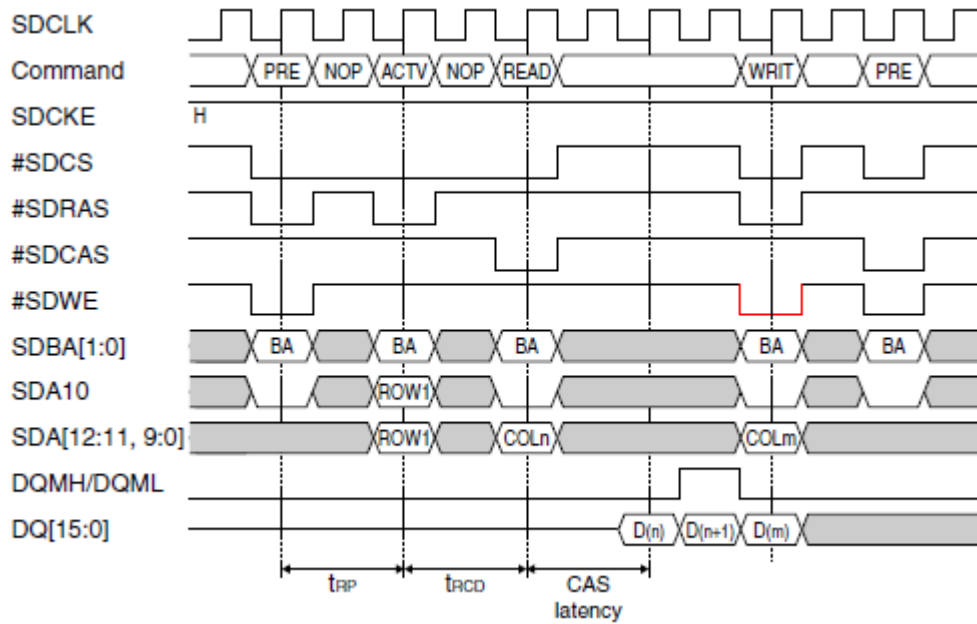
ITEM Control and Operation of SDRAM Interface			
Object manual	Document code	Object item	Page
S1C33E07 Technical Manual	410573604	II.4 SDRAM Controller (SDRAMC)	II-4-14, 15
S1C33E08 Technical Manual	410865100	II.4 SDRAM Controller (SDRAMC)	II-4-14, 15
S1C33L05 Technical Manual	405262000	VIII-2 SDRAM INTERFACE	VIII-2-15
S1C33L17 Technical Manual	411520600	II.4 SDRAM Controller (SDRAMC)	II-4-14, 15
S1C33L18 Technical Manual	411573200	II.4 SDRAM Controller (SDRAMC)	II-4-14, 15
S1C33L19 Technical Manual	411664200	II.4 SDRAM Controller (SDRAMC)	II-4-14, 15
S1C33L26 Technical Manual	411900101	10 SDRAM Controller (SDRAMC)	10-11, 12
S1C33L27 Technical Manual	411911901	10 SDRAM Controller (SDRAMC)	10-10, 11

Page II-4-14 S1C33E07 Technical Manual
Page II-4-14 S1C33E08 Technical Manual
Page VIII-2-15 S1C33L05 Technical Manual
Page II-4-14 S1C33L17 Technical Manual
Page II-4-14 S1C33L18 Technical Manual
Page II-4-14 S1C33L19 Technical Manual
Page 10-11 S1C33L26 Technical Manual
Page 10-10 S1C33L27 Technical Manual

(Error)

The diagram illustrates the timing relationships between various SDRAM control and data signals. The signals shown are: SDCLK (clock), Command (with phases PRE, NOP, ACTV, NOP, READ, WRIT, PRE), SDCKE (chip enable, high), #SDCS (column select), #SDRAS (row address strobe), #SDCAS (column address strobe), #SDWE (write enable), SDBA[1:0] (bank address, BA), SDA10 (row address, ROW), SDA[12:11, 9:0] (row and column addresses, ROW and COL), DQM/DQML (data mask), and DQ[15:0] (data bus, D(n), D(n+1), D(m)). Timing parameters are indicated: tRP (row precharge time), tRCD (row to column delay), and CAS latency (delay from CAS to data output).

(Correct)



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Page II-4-15 S1C33E08 Technical Manual

Page II-4-15 S1C33L17 Technical Manual

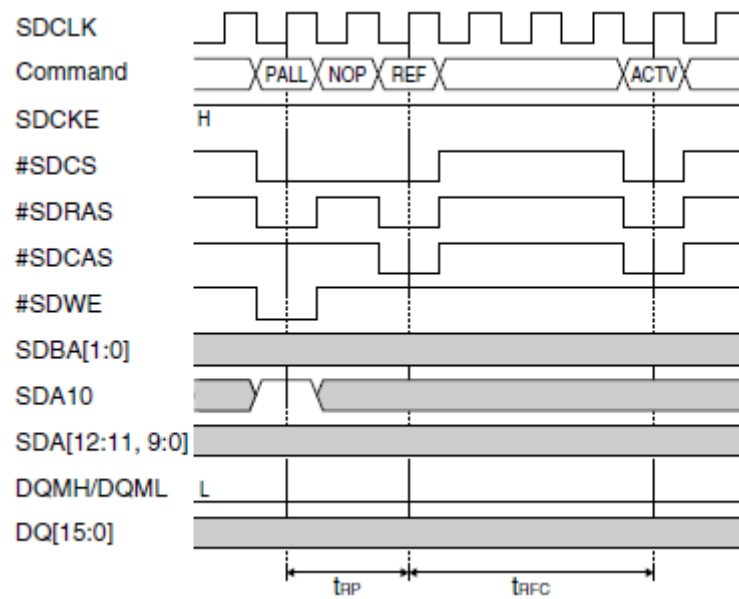
Page II-4-15 S1C33L18 Technical Manual

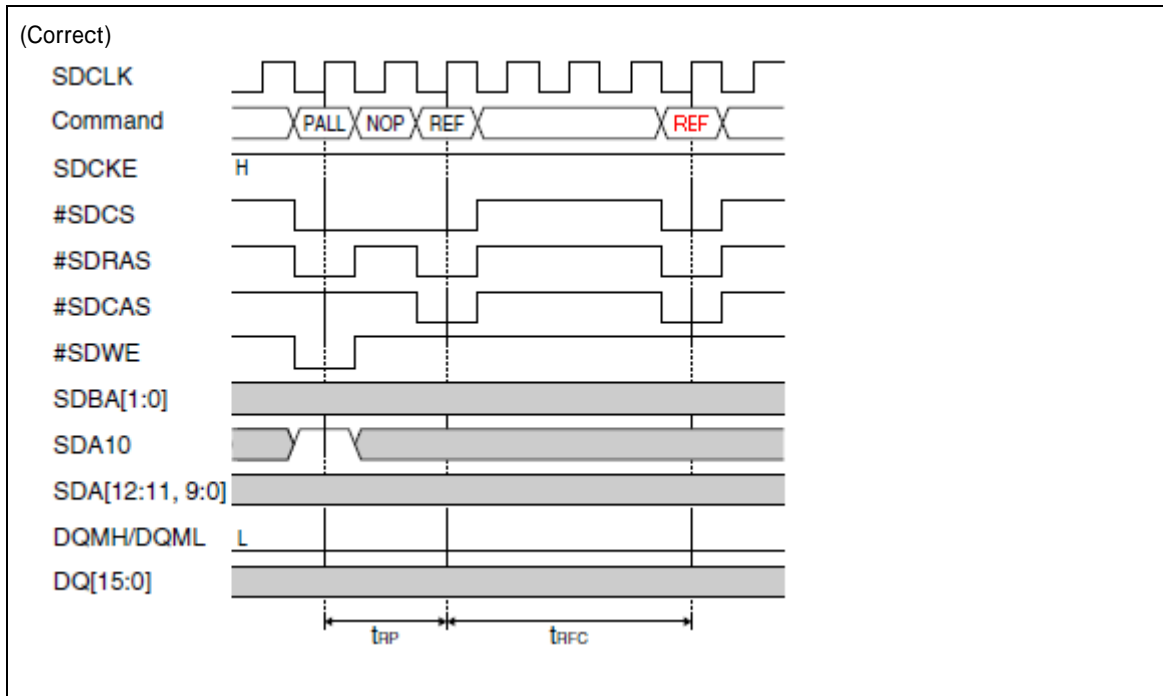
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Page 10-12 S1C33L26 Technical Manual

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S1C33 Manual errata

ITEM: SRAM AC Characteristics			
Object manuals	Document codes	Items	Pages
S1C33L27 Technical Manual	411911901	32.8.2 SRAMC AC Characteristics	32-8

(Error)

Unless otherwise specified: LV_{DD} = 1.65 to 1.95V, HV_{DD} = 2.7 to 3.6V, V_{SS} = 0V, external load = 50pF, Ta = -40 to 85°C

Item	Symbol	Min.	Typ.	Max.	Unit
CMU_CLK output delay time	t _{CD}	–	–	24	ns
Address delay time	t _{AD}	–	–	7	ns
#CE _x delay time	t _{CED}	–	–	7	ns
Write delay time	t _{WRD}	–	–	7	ns
Write data delay time	t _{WRDD}	–	–	7	ns
Write data hold time	t _{WRDH}	1	–	–	ns
Read delay time	t _{RDD}	–	–	7	ns
Read data setup time	t _{RDS}	7	–	–	ns
Read data hold time	t _{RDDH}	0	–	–	ns
Write signal pulse width	t _{WRW}	t _{cyc} (1 + WC) - 7	–	–	ns
Read signal pulse width	t _{RDW}	t _{cyc} (1 + WC) - 7	–	–	ns
Read address access time	t _{ACC}	–	–	t _{cyc} (1 + WC) - 14	ns
Chip enable access time	t _{CEAC}	–	–	t _{cyc} (1 + WC) - 14	ns
Read signal access time	t _{RDAC}	–	–	t _{cyc} (1 + WC) - 14	ns
#WAIT setup time	t _{WTS}	48	–	–	ns
#WAIT hold time	t _{WTH}	0	–	–	ns

WC: Number of wait cycles

(Correct)

Unless otherwise specified: LV_{DD} = 1.65 to 1.95V, HV_{DD} = 2.7 to 3.6V, V_{SS} = 0V, external load = 50pF, Ta = -40 to 85°C

Item	Symbol	Min.	Typ.	Max.	Unit
CMU_CLK output delay time	t _{CD}	–	–	24	ns
SRAM cycle time	t _{CYC}	*	–	–	ns
Address delay time	t _{AD}	–	–	7	ns
#CE _x delay time	t _{CED}	–	–	7	ns
Write delay time	t _{WRD}	–	–	7	ns
Write data delay time	t _{WRDD}	–	–	7	ns
Write data hold time	t _{WRDH}	1	–	–	ns
Read delay time	t _{RDD}	–	–	7	ns
Read data setup time	t _{RDS}	7	–	–	ns
Read data hold time	t _{RDDH}	0	–	–	ns
Write signal pulse width	t _{WRW}	t _{cyc} (1 + WC) - 7	–	–	ns
Read signal pulse width	t _{RDW}	t _{cyc} (1 + WC) - 7	–	–	ns
Read address access time	t _{ACC}	–	–	t _{cyc} (1 + WC) - 14	ns
Chip enable access time	t _{CEAC}	–	–	t _{cyc} (1 + WC) - 14	ns
Read signal access time	t _{RDAC}	–	–	t _{cyc} (1 + WC) - 14	ns
#WAIT setup time	t _{WTS}	48	–	–	ns
#WAIT hold time	t _{WTH}	0	–	–	ns

WC: Number of wait cycles

* : The SRAM cycle time is same as S_{YS}CLK.
The minimum cycle time to output CMU_CLK signal is Min.20.8ns

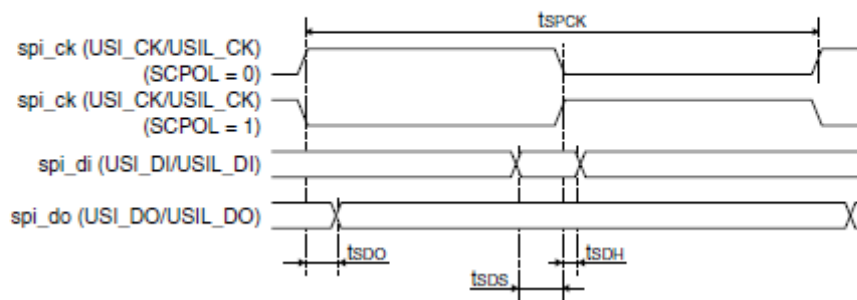
S1C33 Manual errata

ITEM: Modification AC Characteristics about USI SPI slave mode			
Object manuals	Document codes	Items	Pages
S1C33L27 Technical Manual	411911901	32.8.4 USI/USIL AC Characteristics	32-11

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32.8.4 USI/USIL AC Characteristics

SPI master/slave mode (USI/USIL)



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SPI slave mode

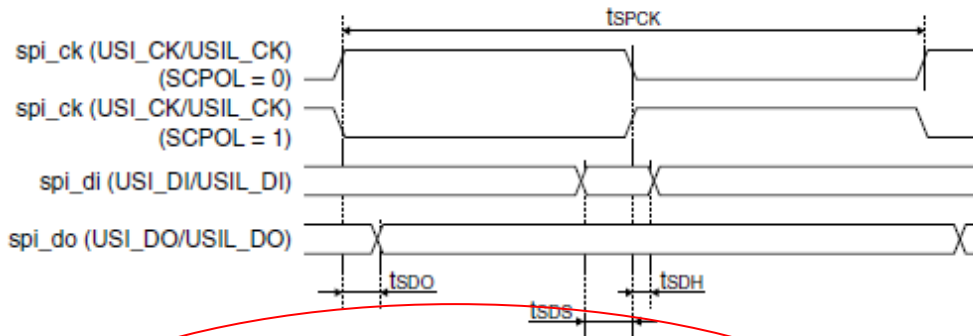
Unless otherwise specified: LVDD = 1.65 to 1.95V, HVDD = 2.7 to 3.6V, VSS = 0V, Ta = -40 to 85°C

Item	Symbol	Min.	Typ.	Max.	Unit
spi_ck cycle time	tSPCK	29 + tPCLK	–	–	ns
spi_di setup time	tSDS	20 + tPCLK	–	–	ns
spi_di hold time	tSDH	9	–	–	ns
spi_do output delay time	tSDO	–	–	42	ns
spi_do output hold time	tSDOH	–	–	2 + tPCLK + 40.552	ns

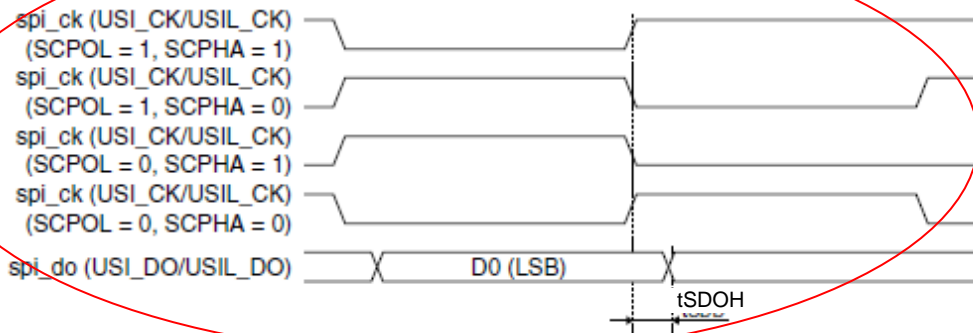
tPCLK: PCLK (peripheral module clock supplied from the CMU) clock cycle time

(Correct)

SPI master/slave mode (USI/USIL)



Last bit output timing in slave mode



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SPI slave mode

Unless otherwise specified: LVDD = 1.65 to 1.95V, HVDD = 2.7 to 3.6V, VSS = 0V, Ta = -40 to 85°C

Item	Symbol	Min.	Typ.	Max.	Unit
spi_ck cycle time	tSPCK	29 + tPCLK	–	–	ns
spi_di setup time	tSDS	20 + tPCLK	–	–	ns
spi_di hold time	tSDH	9	–	–	ns
spi_do output delay time	tSDO	–	–	42	ns
spi_do output hold time	tSDOH	2 * tPCLK	–	–	ns

tPCLK: PCLK (peripheral module clock supplied from the CMU) clock cycle time